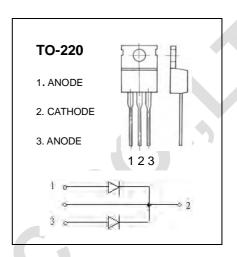




MBR20200CT SCHOTTKY BARRIER RECTIFIER

FEATURES

- · Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- · Low Power Loss, High Efficiency
- · High Surge Capability
- · High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		
Working Peak Reverse Voltage	V_{RWM}	200	V
DC Blocking Voltage	V_R		
Average Rectified Output Current	Io	20	А
(Note 1) @ T _C =125℃			
Non-Repetitive Peak Forward Surge Current	I _{FSM}	150	А
8.3ms Single half sine-wave superimposed on			
rated load (JEDEC Method)			
Repetitive Peak Reverse Surge Current	I _{RRM}	1	Α
@ t≤ 2.0μs			
Forward Voltage Drop @ I _F =10A, T _C =25℃		0.95	V
@I _F =10A, T _C =125℃	V_{FM}	0.8	
@ I _F =20A, T _C =25℃		1.0	
@ I _F =20A, T _C =125℃		0.9	
Peak Reverse Current @ T _C = 25℃	I _{RM}	1	mA
at Rated DC Blocking Voltage @ T _C =125℃	·KIVI	50	
Typical Junction Capacitance (Note 2)	C _j	500	pF
Operating and Storage Temperature Range	T_j , T_{STG}	-65 to +150	℃

Notes: 1. Thermal resistance junction to case mounted heat sink.

2. Measured at 1.OMHz and applied reverse voltage of 4.0V DC.